

<b>Notice of References Cited</b>		Application/Control No.	Applicant(s)/Patent Under Reexamination	
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Examiner		Art Unit		Page 1 of 1
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	B	US-2001/0016420	08-2001	Chou, Ming-Chun	438/687
	C	US-6,773,573	08-2004	Gabe et al.	205/296
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	L	US-			
	M	US-			

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**NON-PATENT DOCUMENTS**

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	V	Itsumi et al., "Gate Oxide Defects in MOSLISIs and Octahedral Void Defects in Czochralski Silicon" Japanes Journal of Applied Physics, vol. 37, pp 1228-1235, March 1998
	W	Park et al., "Nature of Surface and Bulk Defect Induced by Low Dose Oxygen Implantation in Separation by Implanted Oxygen Wafers", Japanese Journal of Applied Physics, vol., 40, pp. 2178-2185, April 2001
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\*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)  
Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.